

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☑ Surface-mounted package
- ☑ Low thermal resistance

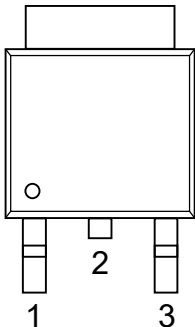
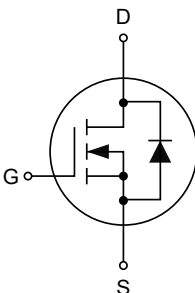
1.2 Applications

- ☑ Battery management
- ☑ Motor control and drive
- ☑ UPS
- ☑ Load switch

1.3 Quick reference

- ☑ $BV \geq 68\text{ V}$
- ☑ $R_{DS(ON)} \leq 7\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☑ $P_D \leq 92.6\text{ W}$
- ☑ $R_{DS(ON)} \leq 14\text{ m}\Omega @ V_{GS} = 6\text{ V}$
- ☑ $I_D \leq 88\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TO-252	
2	Drain(D)		
3	Source(S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	68	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
$I_D^{*,***}$	Drain Current (DC)	$T_C=25^{\circ}\text{C}$	-	88	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	56	A
I_{DM}^{*}	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	352	A
P_D^{*}	Drain Power Dissipation	$T_C=25^{\circ}\text{C}$	-	92.6	W
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=48\text{ V}, L=0.5\text{ mH}$	-	420	mJ
I_S	Continuous-Source Current	$T_C=25^{\circ}\text{C}$	-	88	A
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	150	$^{\circ}\text{C}$
$R_{\theta JA}^{*}$	Thermal Resistance-Junction to Ambient		-	65	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}^{*}$	Thermal Resistance-Junction to Case		-	1.35	

Notes:

* Surface mounted on 1 in² pad area, $t \leq 10\text{ sec}$.

** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

*** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ6880K	KJ6880K XXXXXX

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ6880K	TO-252	13"	16 mm	2500

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	68	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2	-	4	V
I _{DSS}	Drain Leakage Current	V _{DS} =60 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} =±20 V, V _{DS} =0 V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-State Resistance	V _{GS} =10 V, I _{DS} =45 A	-	6	7	mΩ
		V _{GS} =6 V, I _{DS} =30 A	-	11	14	mΩ
R _g	Gate resistance	V _{GS} =0 V, V _{DS} =0 V, f=1 MHz	-	0.9	-	Ω
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =45 A, V _{GS} =0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =45 A, V _{DS} =60 V, dI _{SD} /dt=100 A/μs	-	35	-	ns
Q _{rr}	Reverse Recovery Charge		-	43	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =30 V, f=1 MHz	-	5400	-	pF
C _{oss}	Output Capacitance		-	285	-	
C _{rss}	Reverse Transfer Capacitance		-	200	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =30 V, V _{GEN} =10 V, R _G =3 Ω, I _{DS} =45 A	-	21	-	ns
t _r	Turn-on Rise Time		-	32	-	
t _{d(off)}	Turn-off Delay Time		-	44	-	
t _f	Turn-off Fall Time		-	15	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =30 V, V _{GS} =10 V, I _{DS} =45 A	-	95	-	nC
Q _{gs}	Gate-Source Charge		-	30	-	
Q _{gd}	Gate-Drain Charge		-	25	-	

Notes:

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

7. Typical Characteristics

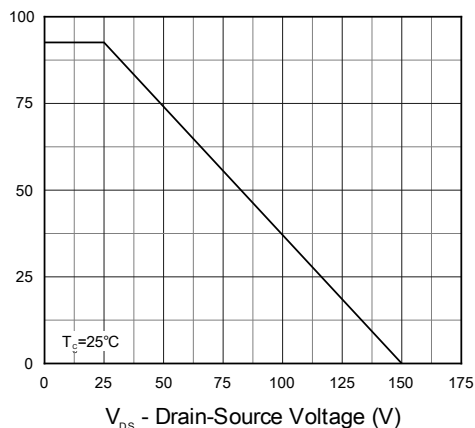


Figure 1. Power Capability

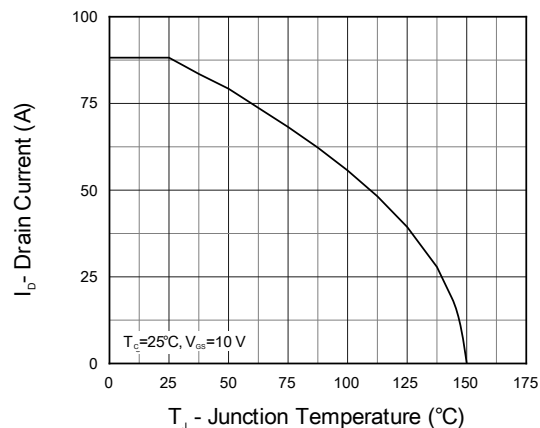


Figure 2. Current Capability

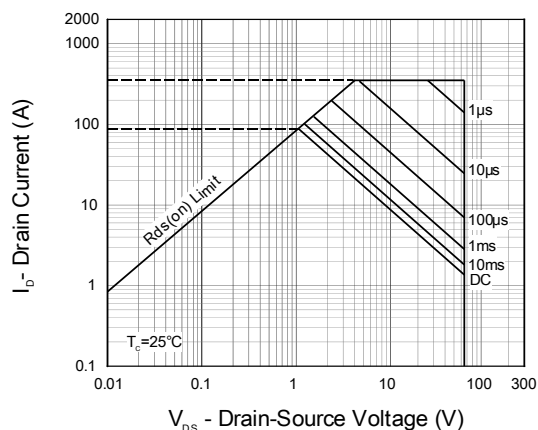


Figure 3. Safe Operation Area

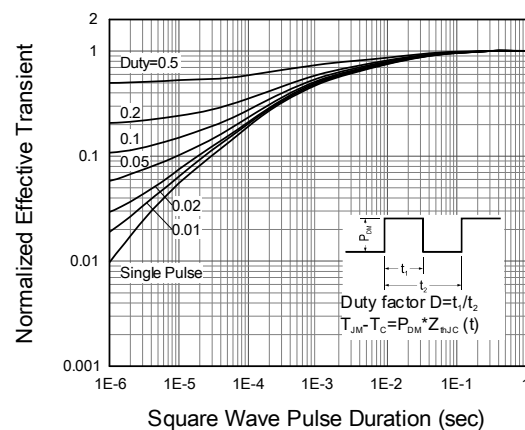


Figure 4. Transient Thermal Impedance

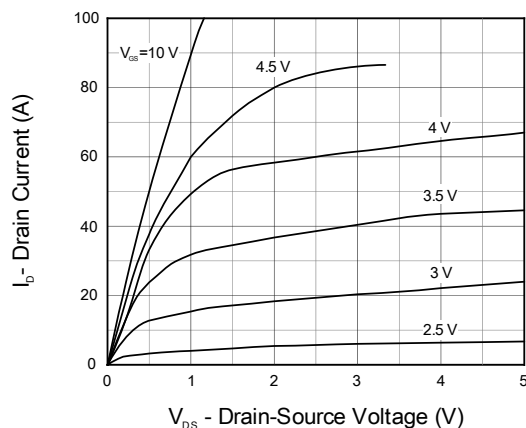


Figure 5. Output Characteristics

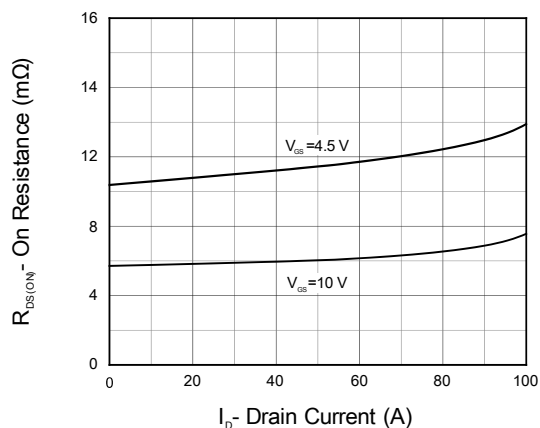


Figure 6. On Resistance

7. Typical Characteristics (cont.)

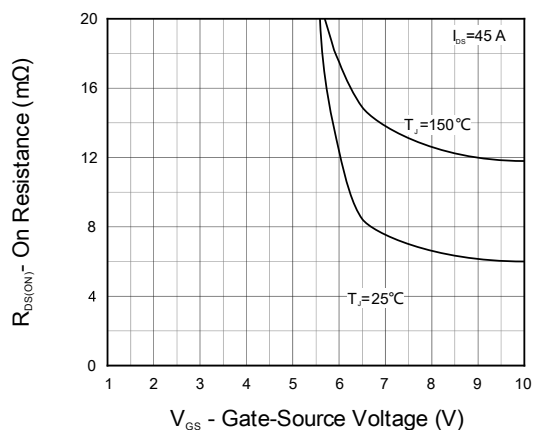


Figure 7. Transfer Characteristics

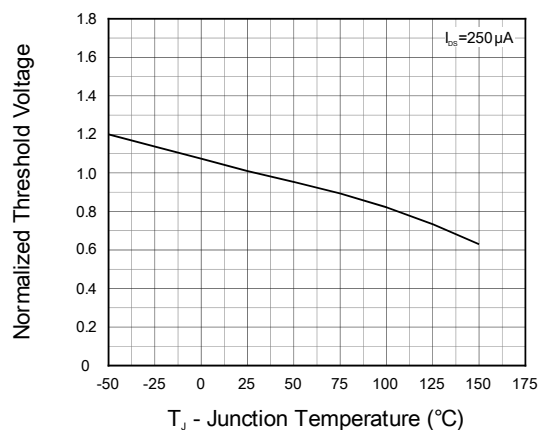


Figure 8. Normalized Threshold Voltage

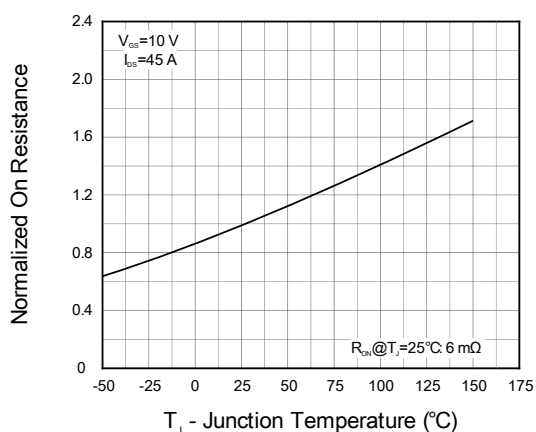


Figure 9. Normalized On Resistance

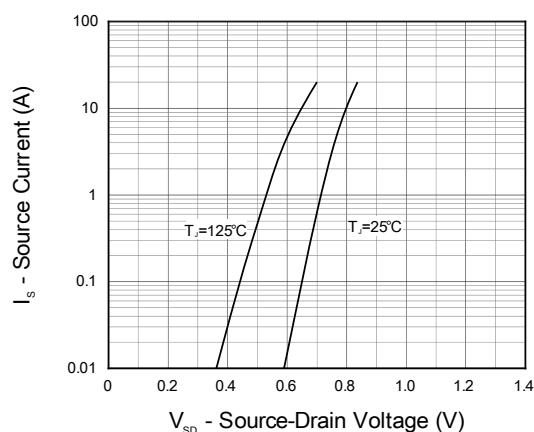


Figure 10. Diode Forward Current

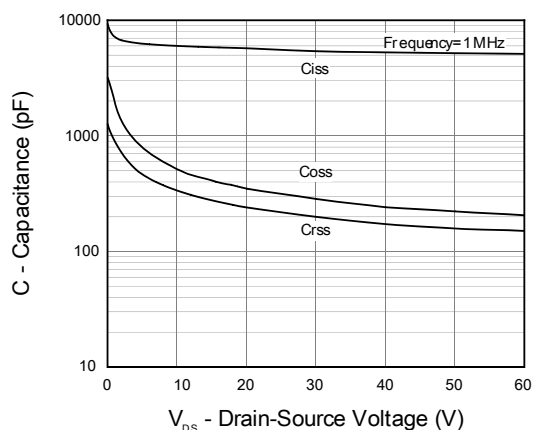


Figure 11. Capacitance

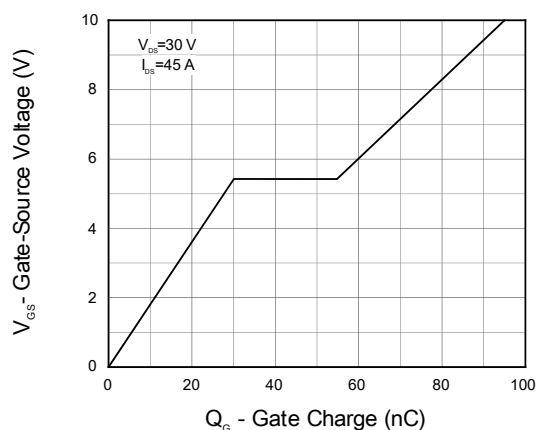
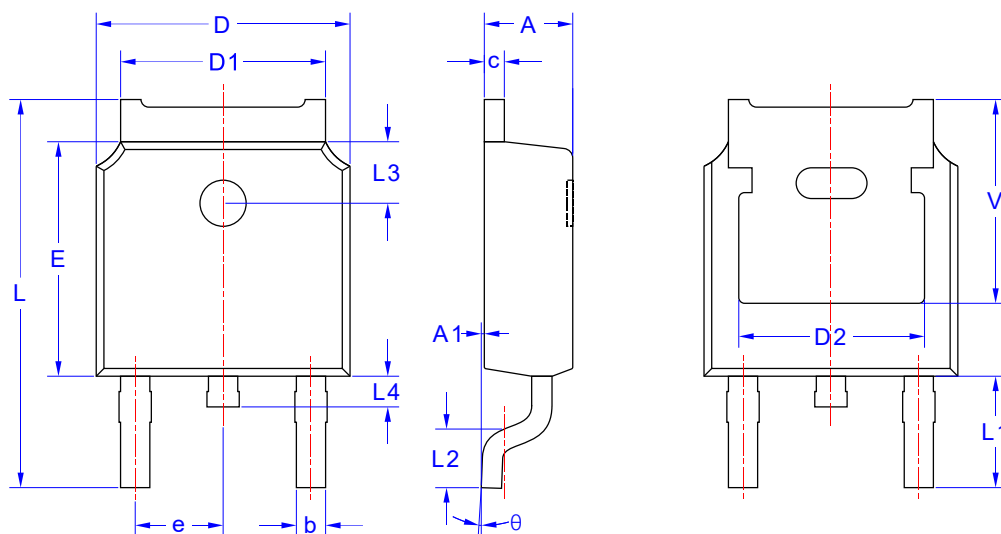


Figure 12. Gate Charge

8. Package Dimensions

TO-252 Package



Symbol	Dimensions in Millimeters	
	MIN	MAX
A	2.200	2.400
A1	0	0.127
b	0.660	0.860
c	0.460	0.580
D	6.500	6.700
D1	5.100	5.460
D2	4.830 REF.	
E	6.000	6.200
e	2.186	2.386
L	9.800	10.400
L1	2.900 REF.	
L2	1.400	1.700
L3	1.800 REF.	
L4	0.600	1.000
θ	0°	8°
V	5.600 REF.	